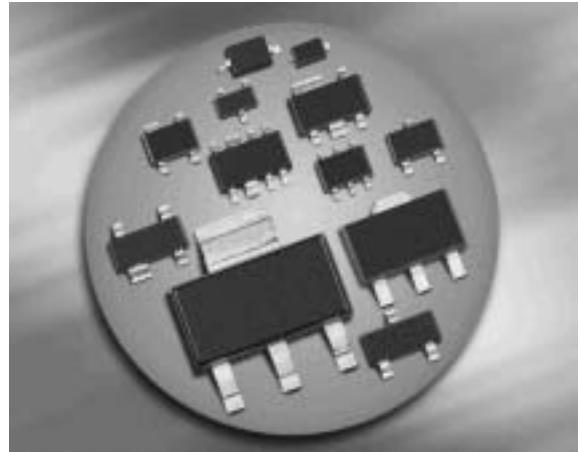
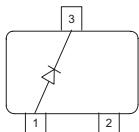


Silicon Switching Diode

- For high-speed switching applications



SMBD914/MMBD914



Type	Package	Configuration	Marking
SMBD914/MMBD914	SOT23	single	s5D
Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified			
Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	100	V
Peak reverse voltage	V_{RM}	100	
Forward current	I_F	250	mA
Repetitive peak forward current	I_{FRM}	-	-
Non-repetitive peak surge forward current $t = 1 \mu\text{s}$	I_{FSM}	4.5	A
$t = 1 \text{ s}$		0.5	
Total power dissipation $T_S \leq 54^\circ\text{C}$	P_{tot}	370	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

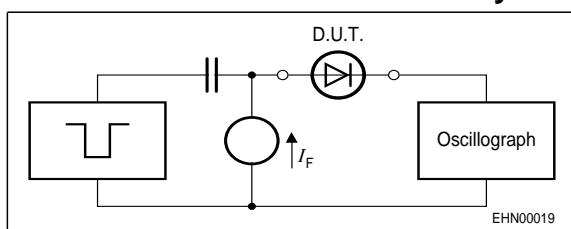
Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 260	K/W
SMBD914/MMBD914			

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(\text{BR})}$	100	-	-	V
Reverse current $V_R = 20 \text{ V}$ $V_R = 75 \text{ V}$ $V_R = 20 \text{ V}, T_A = 150^\circ\text{C}$ $V_R = 75 \text{ V}, T_A = 150^\circ\text{C}$	I_R	-	-	0.025 0.1 30 50	μA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 150 \text{ mA}$	V_F	-	-	715 855 1000 1200 1250	mV
AC Characteristics					
Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	-	2	pF
Reverse recovery time $I_F = 10 \text{ mA}, I_R = 10 \text{ mA}$, measured at $I_R = 1 \text{ mA}$, $R_L = 100 \Omega$	t_{rr}	-	-	4	ns

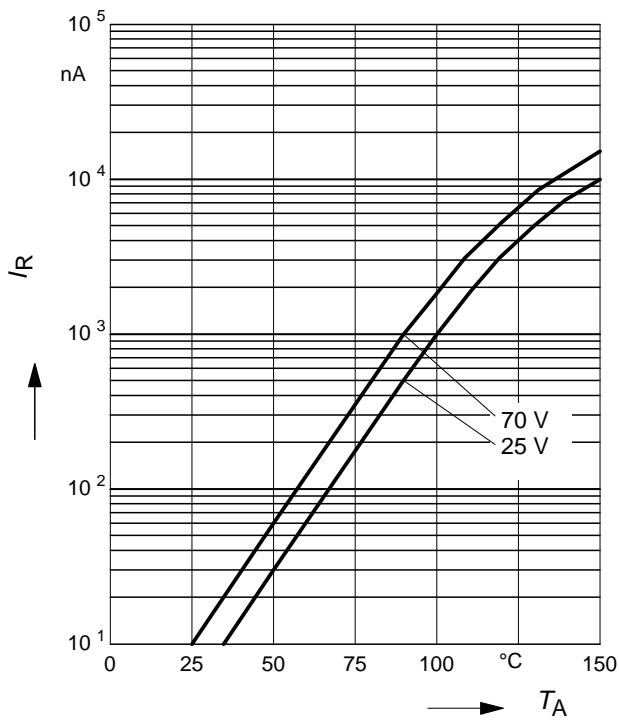
Test circuit for reverse recovery time


Pulse generator: $t_p = 100\text{ns}$, $D = 0.05$, $t_f = 0.6\text{ns}$,
 $R_i = 50\Omega$

Oscilloscope: $R = 50\Omega$, $t_r = 0.35\text{ns}$, $C \leq 1\text{pF}$

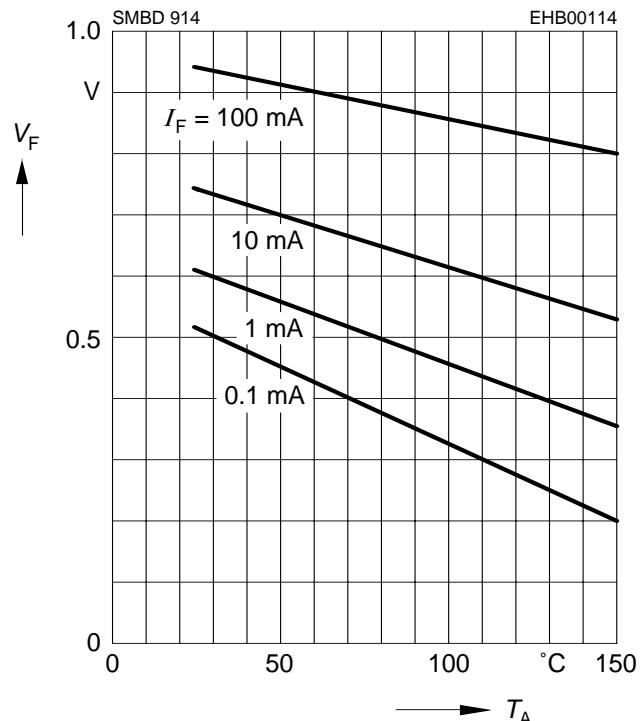
Reverse current $I_R = f(T_A)$

V_R = Parameter



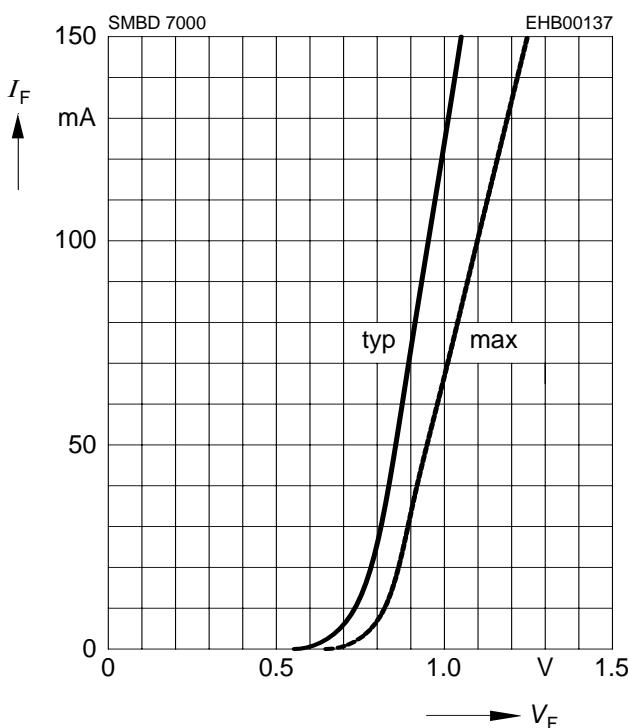
Forward Voltage $V_F = f(T_A)$

I_F = Parameter



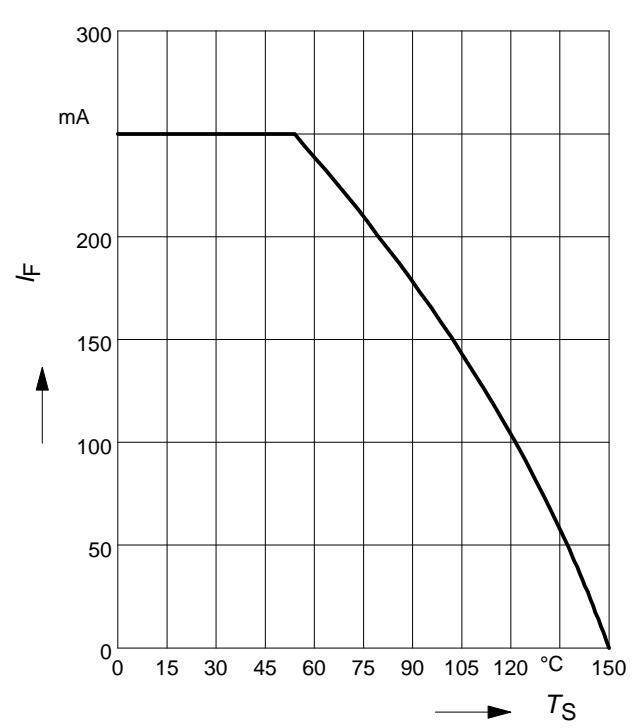
Forward current $I_F = f(V_F)$

$T_A = 25^\circ\text{C}$

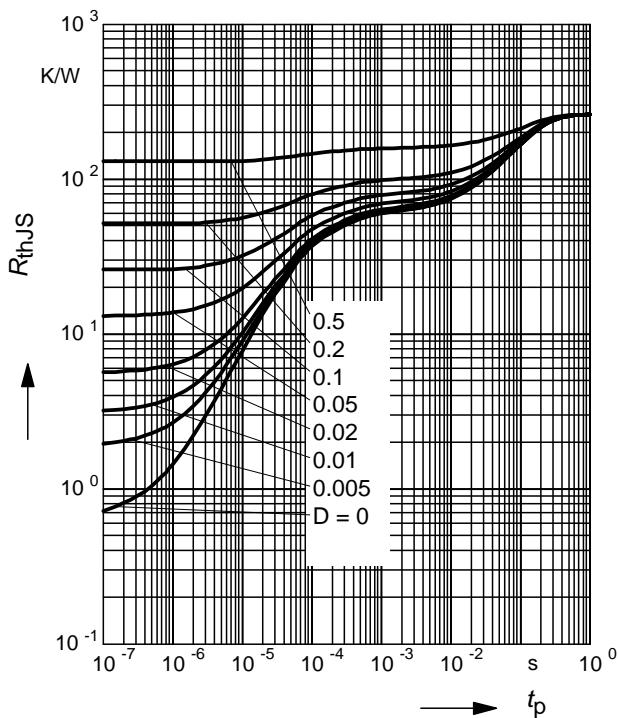


Forward current $I_F = f(T_S)$

SMBD914/MMBD914

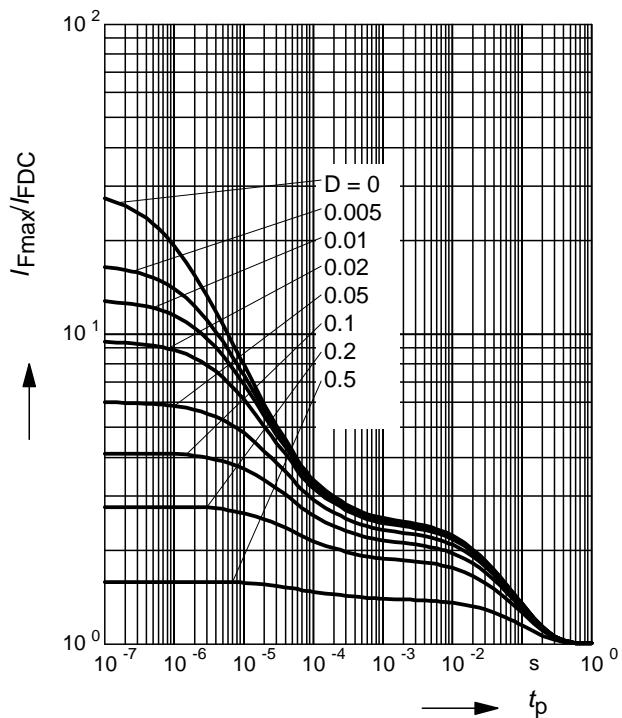


Permissible Puls Load $R_{\text{thJS}} = f(t_p)$

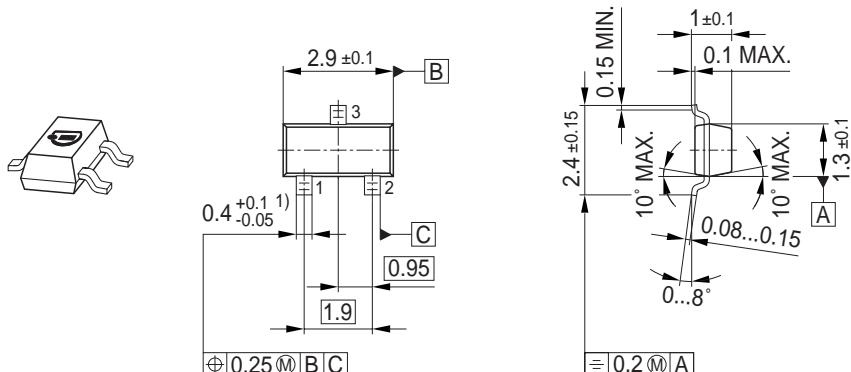


Permissible Pulse Load

$$I_{\text{Fmax}} / I_{\text{FDC}} = f(t_p)$$

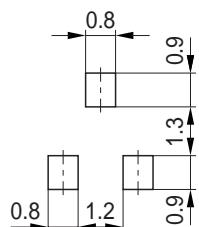


Package Outline

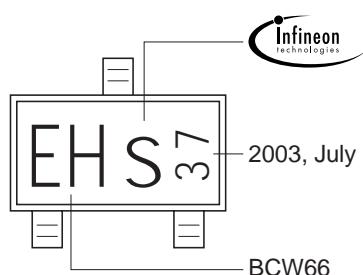
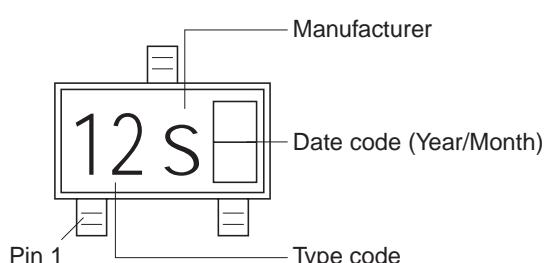


1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout

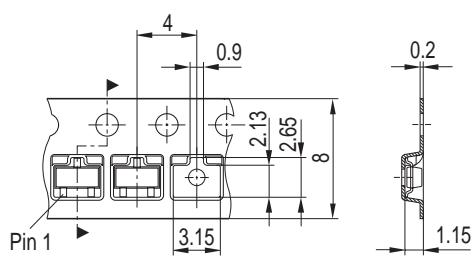


Example

Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

Reel ø330 mm = 10.000 Pieces/Reel



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